

FDC2612

N-Channel PowerTrench[®] MOSFET 200V 1.1A, 725mΩ

Product Overview

For complete documentation, see the data sheet.

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low RDS(ON) and fast switching speed.

Features

- 1.1 A, 200V
- RDS(on) = 725 mΩ @ VGS = 10 V
- High performance trench technology for extremely low RDS(ON)
- High power and current handling capability
- Fast switching speed
- Low gate charge (8nC typical)

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DSS} (BR) Min (V)	V _{GS} Max (V)	V _{GS(t)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
FDC2612	0.3299		Active	N-Channel	Single	200	±20	4.5	1.1	1.6	-	-	725	-	8	234	TSOT-23-6